IN THE CLAIMS:

Listing of claims:

1-16. (canceled)

17. (currently amended) A method of manufacturing a semiconductor device ~~according to claim 4, further~~ comprising:

forming an insulating layer above a semiconductor substrate;

forming a conducting region above the insulating layer, the conducting region selected from the group consisting of a gate electrode and an undercoat wiring;

forming a dielectric layer above the conducting region;

forming a film comprising a titanium nitride layer containing oxygen atoms within a range of from 5 to 25 atomic %;

forming an electrode for a capacitive element above the dielectric layer by processing the film;

forming an out-going electrode connected to the electrode for the capacitive element; and

forming at least one of a resistance element and a fuse element, wherein the electrode for the capacitive element has the same composition as that of the at least one of a resistance element and a fuse element.

18. (currently amended) A method of manufacturing a semiconductor device ~~according to claim 4, further~~ comprising:

forming an insulating layer above a semiconductor substrate;

forming a conducting region above the insulating layer, the conducting region selected from the group consisting of a gate electrode and an undercoat wiring;

forming a dielectric layer above the conducting region;

forming a film comprising a titanium nitride layer containing oxygen atoms within a range of from 5 to 25 atomic %;

forming an electrode for a capacitive element above the dielectric layer by processing the film;

forming an out-going electrode connected to the electrode for the capacitive element; and

forming the electrode for the capacitive element simultaneously with the one of a resistance element and a fuse element.

19-20. (canceled)